19-4809; Rev 0; 8/09

EVALUATION KIT AVAILABLE

Triple High-Voltage Scan Driver for TFT LCD

MAX17120

General Description

The MAX17120 includes three high-voltage level-shifting scan drivers for TFT panel integrated gate logic. Each scan driver has two channels that switch complementarily. The scan-driver outputs swing from +40V to -30V and can swiftly drive capacitive loads. To save power, the scan-driver's complementary outputs share the charge of their capacitive load before they change states.

The MAX17120 is available in a 32-pin, 5mm x 5mm thin QFN package with a maximum thickness of 0.8mm for ultra-thin LCD panels.

Applications

Notebook Computer Displays

LCD Monitor and Small TV Panels

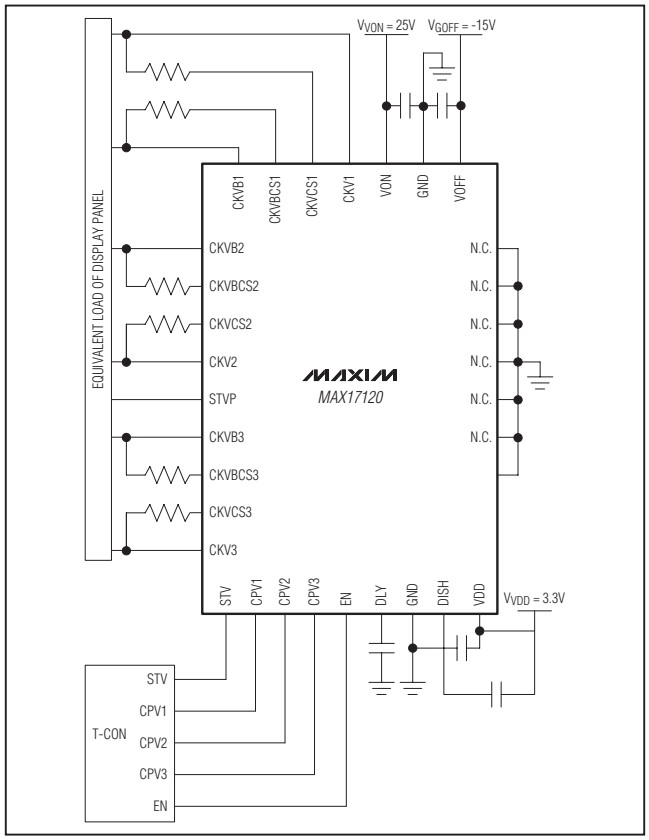
Features

- **+40V to -30V Output Swing Range**
- **Fast Slew Rate for High Capacitive Load**
- **Load Charge Sharing for Power Saving**
- **32-Pin, 5mm x 5mm Thin QFN Package**

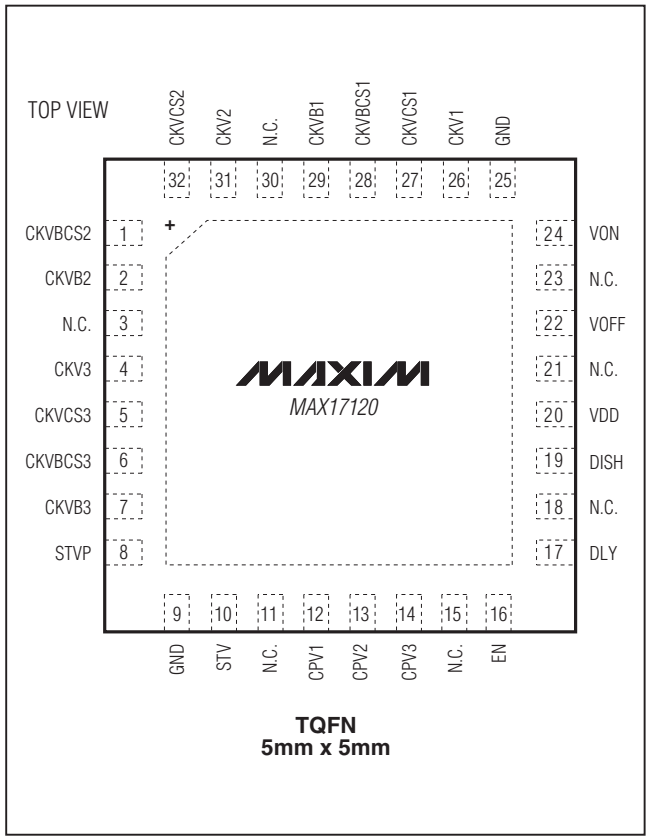
Ordering Information

PART	TEMP RANGE	PIN-PACKAGE
MAX17120ETJ+	-40°C to +85°C	32 TQFN

Simplified Operating Circuit



Pin Configuration



TQFN
5mm x 5mm

Triple High-Voltage Scan Driver for TFT LCD

ABSOLUTE MAXIMUM RATINGS

VDD to GND .....-0.3V to +4V
CPV1, CPV2, CPV3, STV, EN to GND .....-0.3V to +4V
DLY to GND .....-0.3V to (V_{VDD} + 0.3V)
DISH to GND .....-6V to (V_{VDD} + 0.3V)
VON to GND .....-0.3V to +45V
VOFF to GND .....-35V to +0.3V
VON to VOFF ..... +65V
CKV1, CKV2, CKV3, CKVB1, CKVB2,
CKVB3 to VOFF ..... -0.3V to (V_{VON} + 0.3V)
STVP to VOFF ..... -0.3V to (V_{VON} + 0.3V)
CKVCS1, CKVCS2, CKVCS3 to VOFF ... -0.3V to (V_{VON} + 0.3V)
CKVBCS1, CKVBCS2,
CKVBCS3 to VOFF ..... -0.3V to (V_{VON} + 0.3V)
Continuous Power Dissipation (T_A = +70°C)
32-Pin 5mm x 5mm Thin QFN
(derate 34.5mW/°C above +70°C) 2758.6mW
Operating Temperature Range ..... -40°C to +85°C
Junction Temperature .....+150°C
Storage Temperature Range..... -65°C to +150°C
Lead Temperature (soldering, 10s) .....+300°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

(V_{VDD} = V_{EN} = +3.3V, V_{VON} = 25V, V_{VOFF} = -15V, STV = CPV1 = CPV2 = CPV3 = GND, **T_A = 0°C to +85°C**, unless otherwise noted. Typical values are at T_A = +25°C.)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
VDD Input-Voltage Range		2.2		3.6	V
VDD UV Lockout	Rising, hysteresis = 150mV		2	2.15	V
VDD Quiescent Current	V_{EN} = 3.3V		500	750	µA
	EN = GND		500	750	
Thermal Shutdown	Rising edge, hysteresis = 15°C		160		°C
VON Input-Voltage Range		15		40	V
VON Supply Current	V_{EN} = 3.3V		300	600	µA
	EN = GND		300	600	
VOFF Input-Voltage Range		-30		-3	V
VOFF Supply Current	V_{EN} = 3.3V		200	350	µA
	EN = GND		200	350	
VON-to-VOFF Voltage Range				65	V
VON UV Lockout	VON rising		12	13	V
	VON falling	10	11		
CKV_, CKVB_ Output Low	I(CKV_) = -20mA		5	10	Ω
CKV_, CKVB_ Output High	I(CKV_) = 20mA		9	18	Ω
CPV_ Rising to CKV_ Rising	t_R, Figure 4, V_{STV} = 0V		100	150	ns
CPV_ Rising to CKV_ Falling	t_F, Figure 4, V_{STV} = 0V		100	150	ns
CPV_ Rising to CKVB_ Rising	t_R, Figure 4, V_{STV} = 0V		100	150	ns
CPV_ Rising to CKVB_ Falling	t_F, Figure 4, V_{STV} = 0V		100	150	ns
CPV_ Falling to CKVCS_ Rising	t_{CSR}, Figure 4, V_{STV} = 0V		130	180	ns
CPV_ Falling to CKVCS_ Falling	t_{CSF}, Figure 4, V_{STV} = 0V		130	180	ns
CPV_ Falling to CKVCBS_ Rising	t_{CSR}, Figure 4, V_{STV} = 0V		130	180	ns
CPV_ Falling to CKVBCS_ Falling	t_{CSF}, Figure 4, V_{STV} = 0V		130	180	ns

ELECTRICAL CHARACTERISTICS (continued)

(V_{VDD} = V_{EN} = +3.3V, V_{VON} = 25V, V_{VOFF} = -15V, STV = CPV1 = CPV2 = CPV3 = GND, **T_A = 0°C to +85°C**, unless otherwise noted. Typical values are at T_A = +25°C.)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
CKV_, CKVB_ Slew Rate Rising	STV = GND, C_{LOAD} = 15nF, R_{LOAD} = 100Ω, 15% to 85% (Note 1)	100	1000		V/µs
	STV = GND, C_{LOAD} = 4.7nF, 20% to 80%	100	160		
CKV_, CKVB_ Slew Rate Falling	STV = GND, C_{LOAD} = 15nF, R_{LOAD} = 100Ω, 85% to 15% (Note 1)	100	1000		V/µs
	STV = GND, C_{LOAD} = 4.7nF, 80% to 20%	100	160		
CKV_, CKVB_ Slew Rate Rising	STV = VDD, C_{LOAD} = 15nF, R_{LOAD} = 100Ω, 15% to 85% (Note 1)	100	1000		V/µs
	STV = VDD, C_{LOAD} = 4.7nF, 20% to 80%	100	160		
CKV_, CKVB_ Slew Rate Falling	STV = VDD, C_{LOAD} = 15nF, R_{LOAD} = 100Ω, 85% to 15% (Note 1)	100	1000		V/µs
	STV = VDD, C_{LOAD} = 4.7nF, 80% to 20%	100	160		
Three-State Output Current	CKV = midsupply	-1		+1	µA
CKVCS-to-CKVBCS_ Resistance	I(CKVCS to CKVCSB) = 10mA		40	100	Ω
STVP Output Low	I(STVP) = -20mA		17	35	Ω
STVP Output High	I(STVP) = 20mA		40	70	Ω
STV Rising to STVP Rising	t_{PR}		120	200	ns
STV Falling to STVP Falling	t_{PF}		120	200	ns
STVP Slew Rate Rising	C_{LOAD} = 4.7nF	20	30		V/µs
STVP Slew Rate Falling	C_{LOAD} = 4.7nF	20	30		V/µs
CPV_ Input Frequency				85	kHz
Input Low Voltage	CPV_, STV, EN, 2.2V < V_{VDD} < 3.6V			0.8	V
Input High Voltage	CPV_, STV, EN, 2.2V < V_{VDD} < 3.6V	2			V
Input Hysteresis	CPV_, STV, EN		250		mV
Input Bias Current	$V_{STV\_}$ = 0V or V_{VDD}; $V_{CPV\_}$ = 0V or V_{VDD}	-1		+1	µA
DISH Low Voltage				-1.5	V
DISH High Voltage		-0.5			V
DISH Input Impedance	V_{DISH} = -2V		300	600	kΩ
DISH Switch Resistance	V_{DISH} = -2V		200	500	Ω
	V_{DISH} = 0V		1		MΩ
DLY Output Current	DLY = GND	3	4	5	µA
DLY Sink Current	EN = GND, V_{DLY} = 0.4V	5	8		mA
DLY Enable Threshold	Rising	1.60	1.65	1.70	V
Startup Delay	C(DLY) = 0.1µF		40		ms

Triple High-Voltage Scan Driver for TFT LCD

ELECTRICAL CHARACTERISTICS

(V_{VDD} = V_{EN} = +3.3V, V_{VON} = 25V, V_{VOFF} = -15V, STV = CPV1 = CPV2 = CPV3 = GND, **T_A = -40°C to +85°C**, unless otherwise noted.) (Note 2)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
VDD Input-Voltage Range		2.2		3.6	V
VDD UV Lockout	Rising, hysteresis = 150mV			2.15	V
VDD Quiescent Current	V_{EN} = 3.3V			750	µA
	EN = GND			750	
VON Input-Voltage Range		15		40	V
VON Supply Current	V_{EN} = 3.3V			600	µA
	EN = GND			600	
VOFF Input-Voltage Range		-30		-3	V
VOFF Supply Current	V_{EN} = 3.3V			350	µA
	EN = GND			350	
VON-to-VOFF Voltage Range				65	V
VON UV Lockout	VON rising			13	V
	VON falling	10			
CKV_, CKVB_ Output Low	I(CKV_) = -20mA			10	Ω
CKV_, CKVB_ Output High	I(CKV_) = 20mA			18	Ω
CPV_ Rising to CKV_ Rising	t_R, Figure 4, V_{STV} = 0V			150	ns
CPV_ Rising to CKV_ Falling	t_F, Figure 4, V_{STV} = 0V			150	ns
CPV_ Rising to CKVB_ Rising	t_R, Figure 4, V_{STV} = 0V			150	ns
CPV_ Rising to CKVB_ Falling	t_F, Figure 4, V_{STV} = 0V			150	ns
CPV_ Falling to CKVCS_ Rising	t_{CSR}, Figure 4, V_{STV} = 0V			180	ns
CPV_ Falling to CKVCS_ Falling	t_{CSF}, Figure 4, V_{STV} = 0V			180	ns
CPV_ Falling to CKVCBS_ Rising	t_{CSR}, Figure 4, V_{STV} = 0V			180	ns
CPV_ Falling to CKVBCS_ Falling	t_{CSF}, Figure 4, V_{STV} = 0V			180	ns
CKV_, CKVB_ Slew Rate Rising	STV = GND, C_{LOAD} = 15nF, R_{LOAD} = 100Ω, 15% to 85% (Note 2)	100			V/µs
	STV = GND, C_{LOAD} = 4.7nF, 20% to 80%	100			
CKV_, CKVB_ Slew Rate Falling	STV = GND, C_{LOAD} = 15nF, R_{LOAD} = 100Ω, 85% to 15% (Note 2)	100			V/µs
	STV = GND, C_{LOAD} = 4.7nF, 80% to 20%	100			
CKV_, CKVB_ Slew Rate Rising	STV = VDD, C_{LOAD} = 15nF, R_{LOAD} = 100Ω, 15% to 85% (Note 2)	100			V/µs
	STV = VDD, C_{LOAD} = 4.7nF, 20% to 80%	100			

ELECTRICAL CHARACTERISTICS (continued)

(V_{VDD} = V_{EN} = +3.3V, V_{VON} = 25V, V_{VOFF} = -15V, STV = CPV1 = CPV2 = CPV3 = GND, **T_A = -40°C to +85°C**, unless otherwise noted.) (Note 2)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
CKV_, CKVB_ Slew Rate Falling	STV = VDD, C_{LOAD} = 15nF, R_{LOAD} = 100Ω, 85% to 15% (Note 2)	100			V/µs
	STV = VDD, C_{LOAD} = 4.7nF, 80% to 20%	100			
CKVCS-to-CKVBCS_ Resistance	I(CKVCS to CKVCSB_) = 10mA			100	Ω
STVP Output Low	I(STVP) = -20mA			35	Ω
STVP Output High	I(STVP) = 20mA			70	Ω
STV Rising to STVP Rising	t_{PR}			200	ns
STV Falling to STVP Falling	t_{PF}			200	ns
STVP Slew Rate Rising	C_{LOAD} = 4.7nF	20			V/µs
STVP Slew Rate Falling	C_{LOAD} = 4.7nF	20			V/µs
CPV_ Input Frequency				85	kHz
Input Low Voltage	CPV_, STV, EN, 2.2V < V_{VDD} < 3.6V			0.8	V
Input High Voltage	CPV_, STV, EN, 2.2V < V_{VDD} < 3.6V	2			V
DISH Low Voltage				-1.5	V
DISH High Voltage		-0.5			V
DISH Input Impedance	V_{DISH} = -2V			600	kΩ
DISH Switch Resistance	V_{DISH} = -2V			500	Ω
DLY Output Current	DLY = GND	3		5	µA
DLY Sink Current	EN = GND, V_{DLY} = 0.4V	5			mA
DLY Enable Threshold	Rising	1.60		1.70	V

Note 1: Guaranteed by design, not production tested.

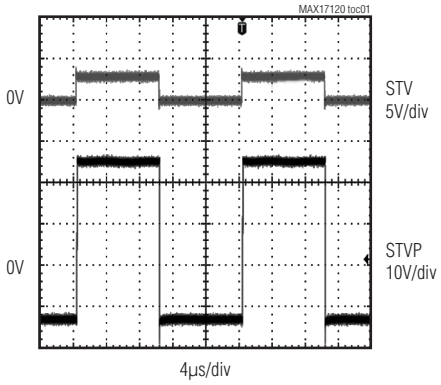
Note 2: Limits are 100% production tested at T_A = +25°C. Maximum and minimum limits over temperature are guaranteed by design and characterization.

Triple High-Voltage Scan Driver for TFT LCD

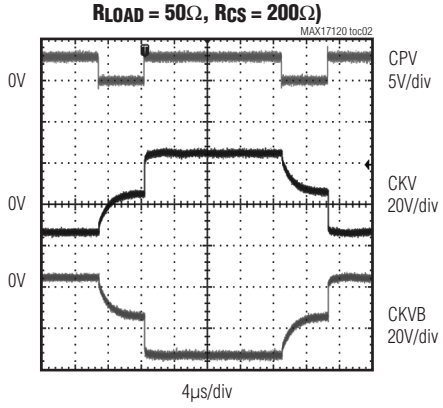
Typical Operating Characteristics

(Circuit of Figure 1, V_{VDD} = V_{EN} = 3.3V, V_{VON} = 25V, V_{VOFF} = -15V, T_A = +25°C, unless otherwise noted.)

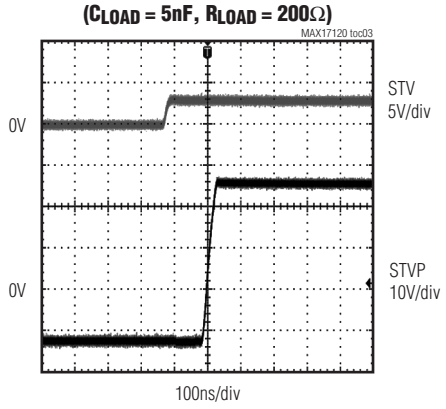
STV/STVP INPUT/OUTPUT WAVEFORMS WITH LOGIC INPUT



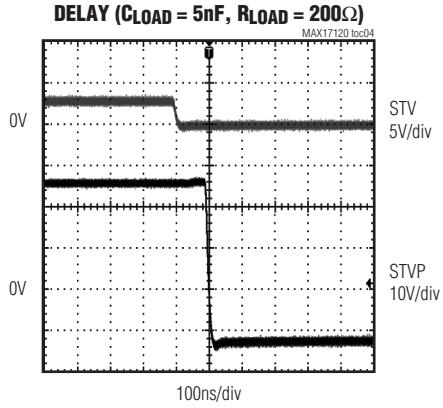
CPV, CKV, AND CKVB INPUT/OUTPUT WAVEFORMS WITH LOGIC INPUT (STV = 0V, C_{LOAD} = 5nF, R_{LOAD} = 50Ω, R_{CS} = 200Ω)



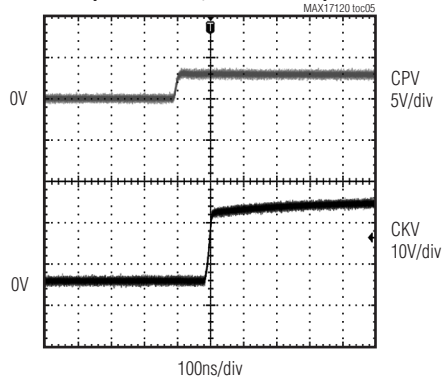
STV RISING EDGE PROPAGATION DELAY (C_{LOAD} = 5nF, R_{LOAD} = 200Ω)



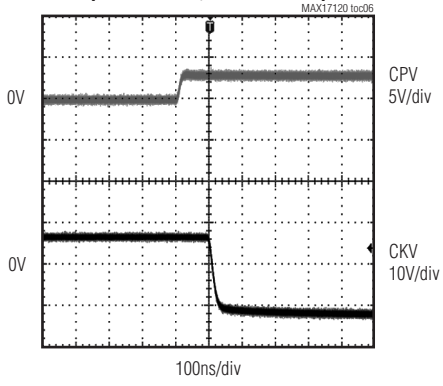
STV FALLING EDGE PROPAGATION DELAY (C_{LOAD} = 5nF, R_{LOAD} = 200Ω)



CPV/CKV RISING EDGE PROPAGATION DELAY (C_{LOAD} = 5nF, R_{LOAD} = 50Ω)



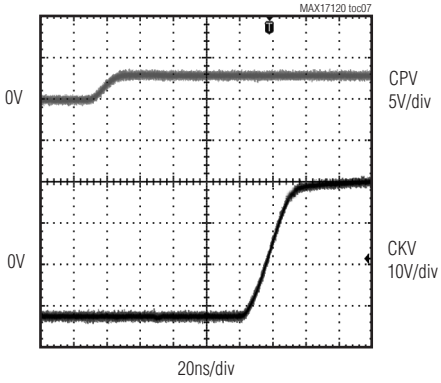
CPV/CKV FALLING EDGE PROPAGATION DELAY (C_{LOAD} = 5nF, R_{LOAD} = 50Ω)



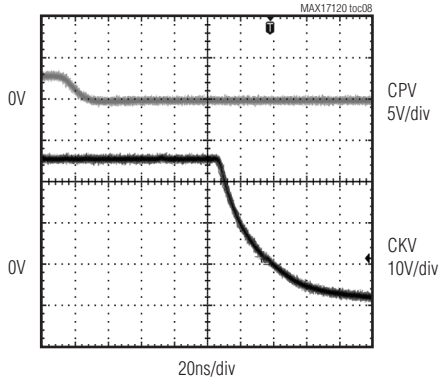
Typical Operating Characteristics (continued)

(Circuit of Figure 1, V_{VDD} = V_{EN} = 3.3V, V_{VON} = 25V, V_{VOFF} = -15V, T_A = +25°C, unless otherwise noted.)

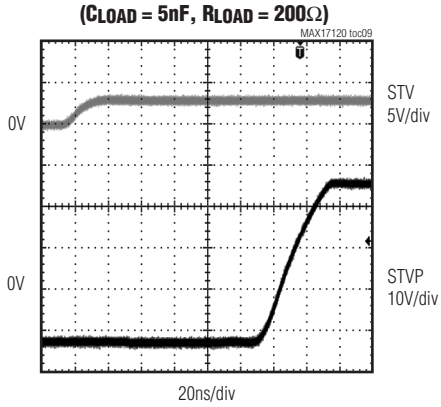
CKV SLEW RATE ON RISING EDGE
(STV = VDD, C_{LOAD} = 5nF, R_{LOAD} = 50Ω)



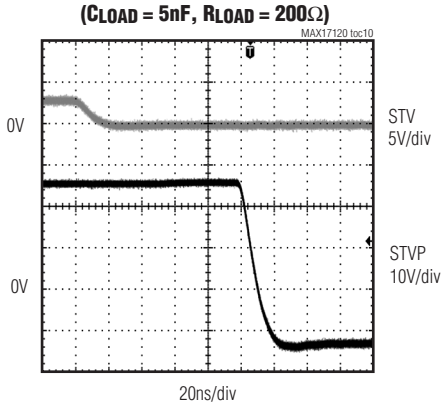
CKV SLEW RATE ON FALLING EDGE
(STV = VDD, C_{LOAD} = 5nF, R_{LOAD} = 50Ω)



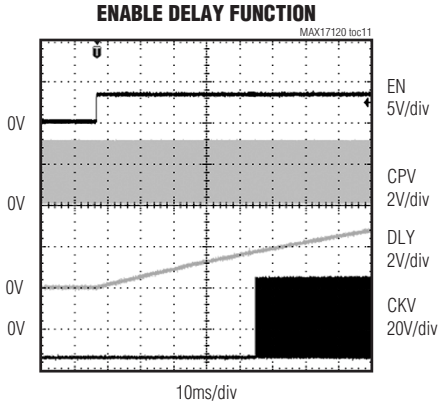
STVP SLEW RATE ON RISING EDGE
(C_{LOAD} = 5nF, R_{LOAD} = 200Ω)



STVP SLEW RATE ON FALLING EDGE
(C_{LOAD} = 5nF, R_{LOAD} = 200Ω)



ENABLE DELAY FUNCTION



Triple High-Voltage Scan Driver for TFT LCD

Pin Description

PIN	NAME	FUNCTION
1	CKVBCS2	CKVB2 Charge-Sharing Connection. CKVBCS2 connects to CKVCS2 whenever CPV2 and STV are both low (to make CKV2 and CKVB2 high impedance) to allow CKV2 to connect to CKVB2, sharing charge between the capacitive loads on these two outputs.
2	CKVB2	High-Voltage Scan-Drive Output. CKVB2 is the inverse of CKV2 during active states and is high impedance whenever CKV2 is high impedance.
3, 11, 15, 18, 21, 23, 30	N.C.	Not connected
4	CKV3	High-Voltage Scan-Drive Output. When enabled, CKV3 toggles between its high state (connected to VON) and its low state (connected to VOFF) on each falling edge of the CPV3 input. Further, CKV3 is high impedance whenever CPV3 and STV are both low.
5	CKVCS3	CKV3 Charge-Sharing Connection. CKVCS3 connects to CKVBCS3 whenever CPV3 and STV are both low (to make CKV3 and CKVB3 high impedance) to allow CKVB3 to connect to CKV3, sharing charge between the capacitive loads on these two outputs.
6	CKVBCS3	CKVB3 Charge-Sharing Connection. CKVBCS3 connects to CKVCS3 whenever CPV3 and STV are both low (to make CKV3 and CKVB3 high impedance) to allow CKV3 to connect to CKVB3, sharing charge between the capacitive loads on these two outputs.
7	CKVB3	High-Voltage Scan-Drive Output. CKVB3 is the inverse of CKV3 during active states and is high impedance whenever CKV3 is high impedance.
8	STVP	High-Voltage Scan-Drive Output. STVP is connected to V_{OFF} when STV is low and is connected to V_{ON} when STV is high and CPV1 is low. When both STV and CPV1 are high, STVP is high impedance.
9	GND	Ground
10	STV	Vertical Sync Input. The rising edge of STV begins a frame of data. The STV input is used to generate the high-voltage STVP output.
12	CPV1	Vertical Clock Pulse Input. CPV1 controls the timing of the CKV1 and CKVB1 outputs, which change state (by first sharing charge) on its falling edge.
13	CPV2	Vertical Clock Pulse Input. CPV2 controls the timing of the CKV2 and CKVB2 outputs, which change state (by first sharing charge) on its falling edge.
14	CPV3	Vertical Clock Pulse Input. CPV3 controls the timing of the CKV3 and CKVB3 outputs, which change state (by first sharing charge) on its falling edge.
16	EN	Enables the MAX17120. Drive EN high to start up the MAX17120 after a delay time, which is set by a capacitor at DLY.
17	DLY	Startup Delay Setting. Connect a capacitor to adjust the delay based on $t_{DELAY} = C_{DLY} \times 410k\Omega$.
19	DISH	VOFF Discharge Connection. Pulling DISH below ground activates an internal connection between VOFF and GND, rapidly discharging the VOFF supply. Typically, DISH is capacitively connected to VDD, so that when VDD falls, VOFF is discharged.
20	VDD	Supply Input. VDD is the logic supply input for the scan driver. Bypass to GND through a minimum 0.1µF capacitor.
22	VOFF	Gate-Off Supply. VOFF is the negative supply voltage for the CKV_, CKVB_, and STVP high-voltage driver outputs. Bypass to GND with a minimum 1µF ceramic capacitor.
24	VON	Gate-On Supply. VON is the positive supply voltage for the CKV_, CKVB_, and STVP high-voltage driver outputs. Bypass to GND with a minimum 1µF ceramic capacitor.

Pin Description (continued)

PIN	NAME	FUNCTION
25	GND	Ground
26	CKV1	High-Voltage Scan-Drive Output. When enabled, CKV1 toggles between its high state (connected to VON) and its low state (connected to VOFF) on each falling edge of the CPV1 input. Further, CKV1 is high impedance whenever CPV1 and STV are both low.
27	CKVCS1	CKV1 Charge Sharing Connection. CKVCS1 connects to CKVBCS1 whenever CPV1 and STV are both low (to make CKV1 and CKVB1 high impedance) to allow CKVB1 to connect to CKV1, sharing charge between the capacitive loads on these two outputs.
28	CKVBCS1	CKVB1 Charge-Sharing Connection. CKVBCS1 connects to CKVCS1 whenever CPV1 and STV are both low (to make CKV1 and CKVB1 high impedance) to allow CKV1 to connect to CKVB1, sharing charge between the capacitive loads on these two outputs.
29	CKVB1	High-Voltage Scan-Drive Output. CKVB1 is the inverse of CKV1 during active states and is high impedance whenever CKV1 is high impedance.
31	CKV2	High-Voltage Scan-Drive Output. When enabled, CKV2 toggles between its high state (connected to VON) and its low state (connected to VOFF) on each falling edge of the CPV2 input. Further, CKV2 is high impedance whenever CPV2 and STV are both low.
32	CKVCS2	CKV2 Charge-Sharing Connection. CKVCS2 connects to CKVBCS2 whenever CPV2 and STV are both low (to make CKV2 and CKVB2 high impedance) to allow CKVB2 to connect to CKV2, sharing charge between the capacitive loads on these two outputs.
—	EP	Exposed Pad. EP is not connected in the IC. The EP should be connected to GND plane on the PCB to improve thermal performance.

Triple High-Voltage Scan Driver for TFT LCD

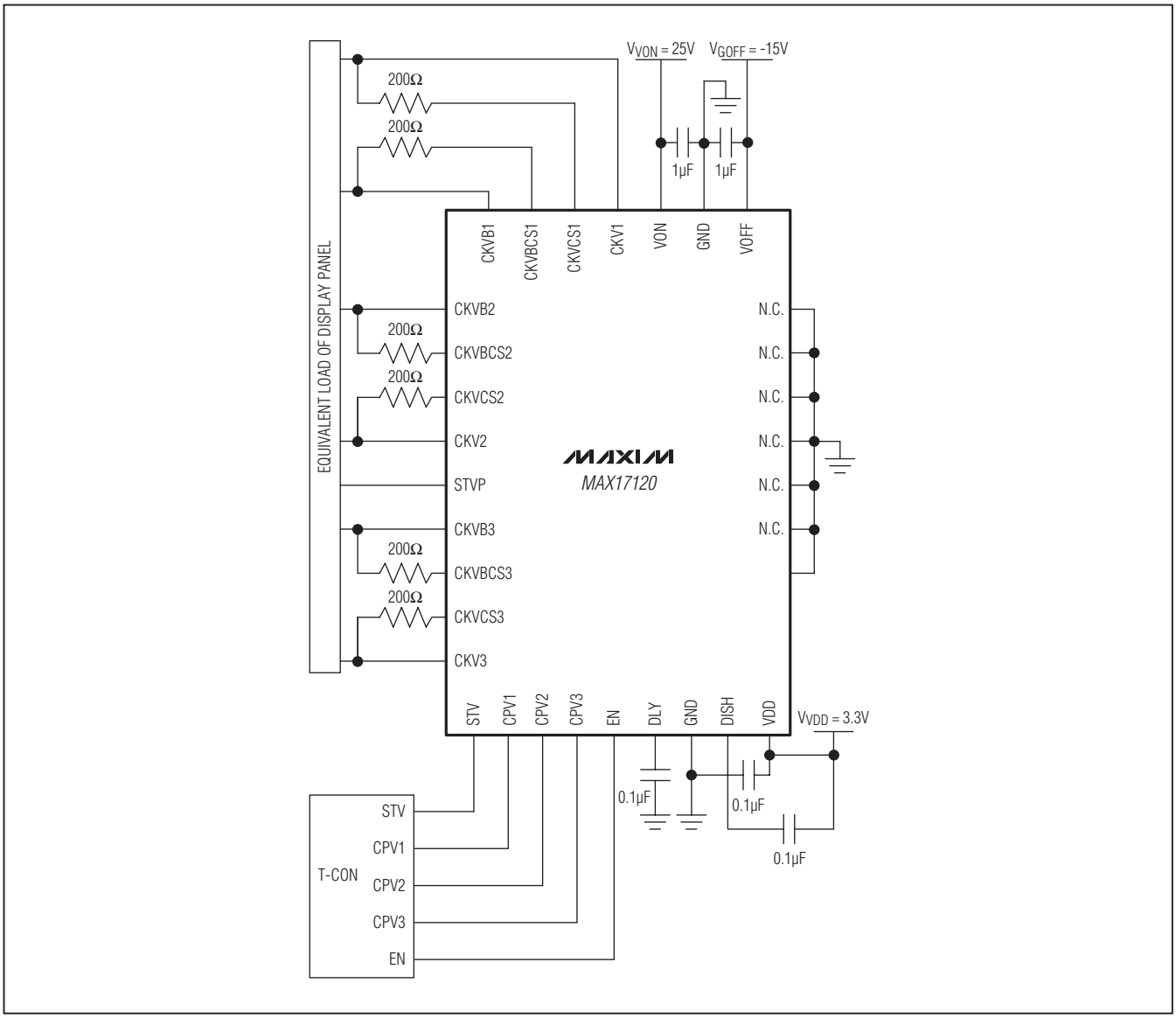


Figure 1. Typical Operating Circuit

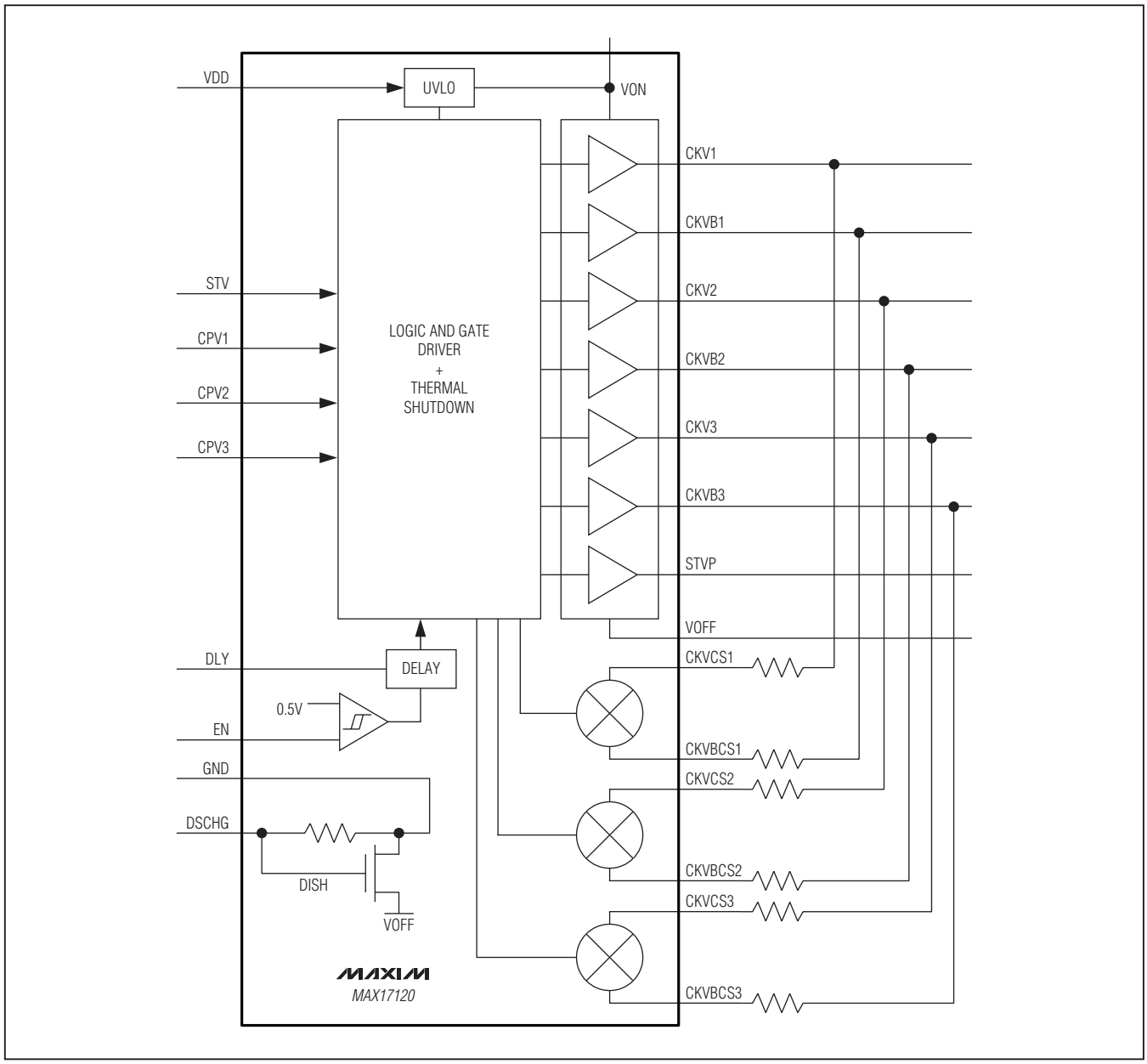


Figure 2. Functional Diagram

Detailed Description

The MAX17120 contains three high-voltage level-shifting scan drivers for active-matrix TFT LCDs. Figure 2 is the functional diagram.

Undervoltage Lockout on VDD

The undervoltage lockout (VDD-UVLO) circuit on VDD compares the input voltage at VDD with the VDD-UVLO (2V typ) to ensure that the input voltage is high enough for reliable operation. There is 100mV of hysteresis to prevent supply transients from causing a restart. When the VDD voltage is below VDD-UVLO, the scan-driver outputs are high impedance.

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Undervoltage Lockout on VON

The undervoltage lockout (VON-UVLO) circuit on V_{ON} compares the input voltage at VON with the VON-UVLO (12V typ) to ensure that the input voltage is high enough for reliable operation. There is 1V of hysteresis to prevent supply transients from causing a restart. When the VON voltage is below VON-UVLO, the scan-driver outputs are high impedance.

High-Voltage Level-Shifting Scan Driver

The MAX17120 includes three high-voltage level-shifting scan drivers. The scan-driver outputs (CKV1, CKV2, CKV3, CKVB1, CKVB2, CKVB3, and STVP) swing between the power-supply rails (VON and VOFF) according to their corresponding input logic levels. The states of the CKV1, CKVB1, and STVP outputs are determined by the input logic levels present on STV and CPV1. The states of the CKV2, CKVB2, and CKV3, CKVB3 outputs are determined by the input logic levels present on STV, CPV2, and STV, CPV3, respectively (see Figure 3, Table 1, and Table 2).

STV is the vertical timing signal. CPV1, CPV2, and CPV3 are the TFT gate logic timing signals. These signals have CMOS input logic levels set by the VDD supply voltage. CKV1, CKV2, and CKV3 are scan clock outputs, which are complementary to scan clock outputs CKVB1, CKVB2, and CKVB3, respectively. These output signals swing from VON to VOFF, which have a maximum upper level of +40V, a minimum lower level of -30V, and a combined maximum range of VON - VOFF = 65V. Their low output impedance enables them to swiftly drive capacitive loads. Input pins CKVCS1, CKVBSC1, CKVCS2, CKVBSC2, CKVCS3, and CKVBCS3 allow the charge in the panel equivalent capacitors to be shared. This reduces the power loss in state transition.

Enable Function

EN is an active-high logic input that enables/disables the MAX17120 output drive. Drive EN high to enable the MAX17120 scan driver. When EN is low, all the drivers' outputs are pulled to VOFF.

Table 1. STVP Logic

VON	EN	V_{DLY}	INPUT SIGNALS		OUTPUT (STVP)
			STV	CPV1	
> UVLO	H	H*	L	X	L
			H	L	H
			H	H	High-Z
		L*	X	X	L
	L	X	X	X	L
< UVLO	X	X	X	X	High-Z

H = high, L = low, high-Z = high impedance, X = Don't care, H = V_{DLY} > 1/2 x VVDD, L* = V_{DLY} < 1/2 x VVDD.*

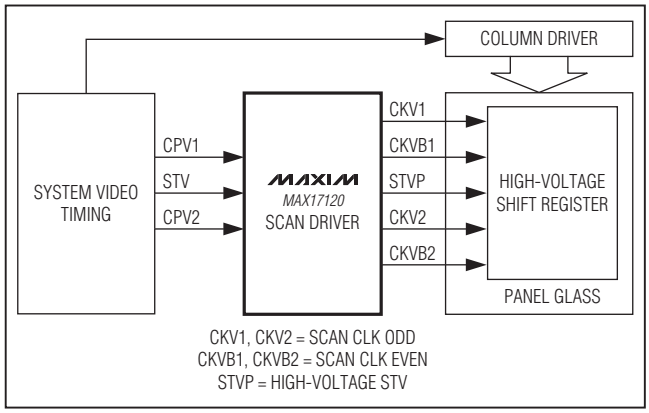

Figure 3. Scan Driver System Diagram

Table 2. CKV_, CKVB_ Logic

VON	EN	V_{DLY}	INPUT SIGNALS		OUTPUTS		
			STV	CPV_	CKV_	CKVB_	CHARGE SHARING
> UVLO	H	H*	L	L	High-Z	High-Z	Yes
			L	↑	Toggle	Toggle	No
			H	L	VOFF	VON	No
			H	H	VON	VOFF	No
		L*	X	X	VOFF	VOFF	No
	Low	X	X	X	VOFF	VOFF	No
< UVLO	X	X	X	X	High-Z		No

H = high, L = low, high-Z = high impedance, ↑ = rising edge, X = Don't care, H = V_{DLY} > 1/2 x VVDD, L x = V_{DLY} < 1/2 x VVDD.*

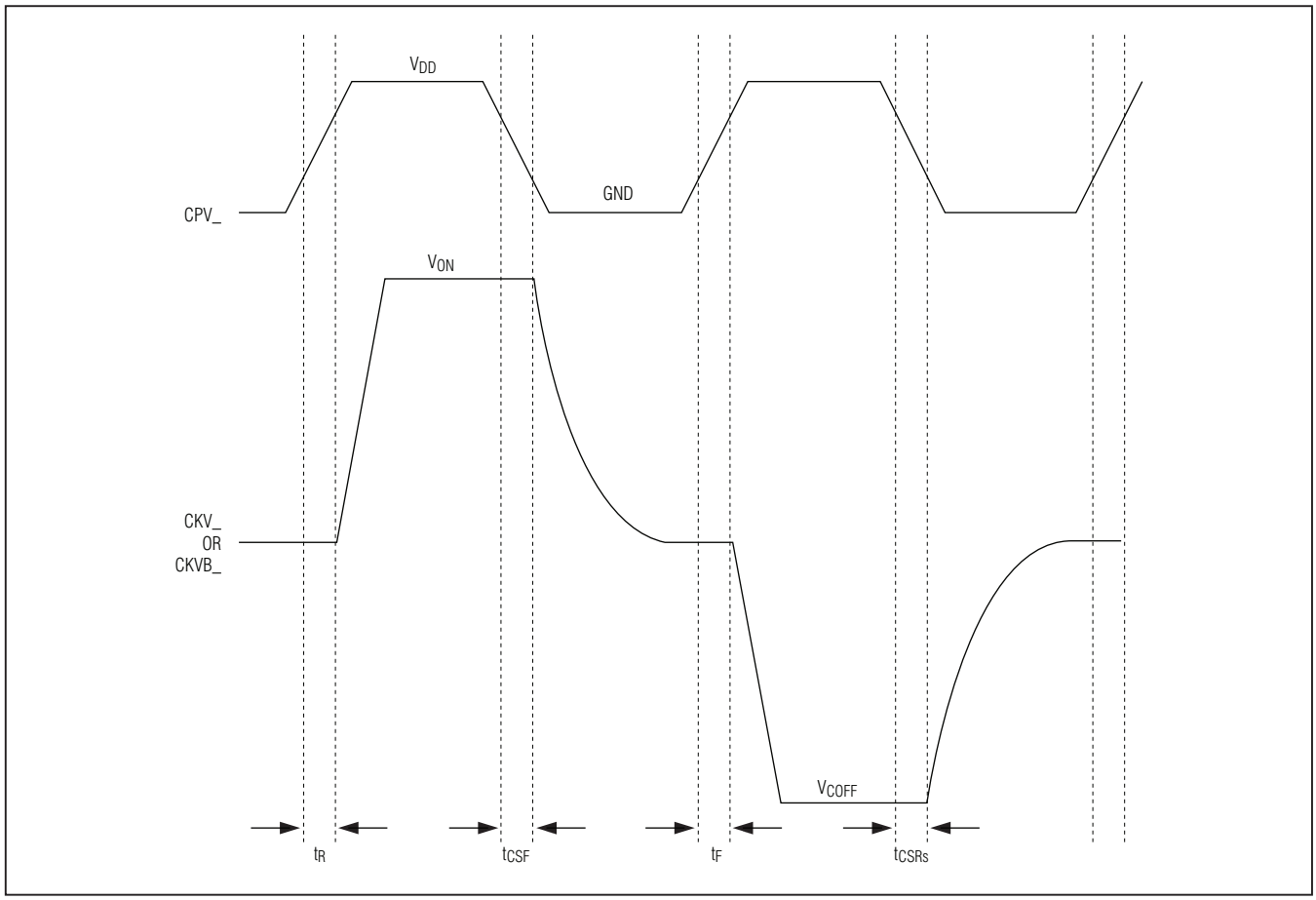

Figure 4. CKV Timing

Delay Function

The DLY input sets the delay time in the startup when the MAX17120 is enabled and the scan-driver outputs are enabled. The delay time is adjustable by choosing a different capacitor at DLY. Calculate the delay capacitance as:

$$C_{DLY} = t_{DELAY}/410k\Omega$$

The delay enable trip point is $V_{VDD}/2$. Before V_{DLY} reaches the threshold, scan-driver outputs stay in the same state as EN is low.

If there is no delay needed in the startup, connect DLY to VDD.

VOFF Rapid-Discharge Function (DISH Input)

The DISH input controls a switch between VOFF and GND. When DISH is pulled below ground by at least 1.5V, VOFF is rapidly discharged to GND. Typically, DISH is capacitively coupled to VDD so that if VDD falls suddenly, VOFF is quickly discharged to GND.

Thermal-Overload Protection

The thermal-overload protection prevents excessive power dissipation from overheating the device. When the junction temperature exceeds T_J = +160°C, a thermal sensor immediately shuts down the scan-driver outputs. The outputs are set to high impedance. Once the device cools down by approximately 15°C, the device reactivates.

The thermal-overload protection protects the IC in the event of overheat conditions. For continuous operation, do not exceed the absolute maximum junction temperature rating of T_J = +150°C.

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Applications Information

Power Dissipation

An IC's maximum power dissipation depends on the thermal resistance from the die to the ambient environment and the ambient temperature. The thermal resistance depends on the IC package, PCB copper area, other thermal mass, and airflow.

The MAX17120, with its exposed backside paddle soldered to 1in^2 of PCB copper, can dissipate approximately 27.8mW into +70°C still air. More PCB copper, cooler ambient air, and more airflow increase the possible dissipation, while less copper or warmer air decreases the IC's dissipation capability.

Scan-Driver Outputs

The power dissipated by the scan-driver outputs (CKV1, CKVB1, STVP, CKV2, and CKVB2), depends on the scan frequency, the capacitive load, and the difference between the VON and VOFF supply voltages. Assuming each output driver is the same capacitance, the power loss is:

$$PD_{SCAN} = 7 \times f_{SCAN} \times C_{PANEL} \times (V_{GON}-V_{GOFF})^2$$

where f_{SCAN} is the scan frequency of the panel, C_{PANEL} is the panel model capacitive load, V_{GON} and V_{GOFF} are the positive gate-on and negative gate-off voltages.

If all the scan drivers operate at a frequency of f_{SCAN} = 50kHz, the load of the six outputs is C_{PANEL} = 5nF, and the supply voltage difference is VON - VOFF = 30V, then the power dissipated is 1.575W.

PCB Layout and Grounding

Careful PCB layout is important for proper operation. Use the following guidelines for good PCB layout:

- Place the VON, VOFF, and VDD pin bypass capacitors as close as possible to the device. The ground connections of the VON, VOFF, and VDD bypass capacitors should be connected directly to the GND pin with a wide trace.
- Avoid using vias in the high-current paths. If vias are unavoidable, use many vias in parallel to reduce resistance and inductance.
- Connect the MAX17120's exposed paddle to GND copper plane and the copper plane area should be maximized to improve thermal dissipation.
- Minimize the length and maximize the width of the traces between the CKV, CKVB, and STV output nodes and the panel load for best transient responses.

Refer to the MAX17120 evaluation kit for an example of proper board layout.

Chip Information

PROCESS: BiCMOS

Package Information

For the latest package outline information and land patterns, go to **www.maxim-ic.com/packages**. Note that a "+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.

PACKAGE TYPE	PACKAGE CODE	DOCUMENT NO.
32 TQFN	T-3225	21-0140